

IN THE CLAIMS

Please cancel claims 1-7, 11-23, and 25-26 without prejudice.

Please amend claims 8-10 and 24.

Please add new claims 27 and 28.

Please enter the pending claims, including claims 8-10, 24, 27, and 28, as follows:

1 1.-7. (Cancelled)

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1 8. (Currently Amended) ~~The~~ A broad-angle multilayer ML mirror of
2 ~~claim 1 comprising a multiple layer structure over a substrate to provide uniform~~
3 ~~reflectivity over a wide range of incident angles with small phase shifts, the~~
4 ~~multiple layer structure comprising Molybdenum/Silicon bi-layers with an extra~~
5 ~~thick layer of Molybdenum next to the substrate wherein the multiple layer~~
6 ~~structure further comprises and~~ an extra thick layer of Silicon near the substrate.

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1 9. (Currently Amended) The broad-angle ML mirror of claim 8 wherein
2 the extra thick layer of Molybdenum is in a first bi-layer over the substrate ~~no. 1.~~

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1 10. (Currently Amended) The broad-angle ML mirror of claim 8 wherein
2 the extra thick layer of Silicon is in a third bi-layer over the substrate ~~no. 3.~~

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1 11.-23. (Cancelled)

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1 24. (Currently Amended) ~~The~~ An optical system of claim 20 having an
2 extreme ultra-violet (EUV) radiation source, the optical system comprising:

3 a mask;

4 a wafer; and

5 a plurality of reflecting surfaces for imaging the mask on the wafer,

6 including:

7 a broad-angle mirror having a multiple layer structure over a substrate to

8 provide uniform reflectivity over a wide range of angles with small phase shifts,

9 the broad-angle mirror comprising bi-layers with an extra thick layer of

10 Molybdenum next to the substrate ~~wherein the broad-angle mirror further~~
11 ~~comprises:~~ and an extra thick layer of Silicon near the substrate.

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1 25.-26. (Cancelled)

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4 27. (New) The optical system of claim 24 wherein the extra thick layer of
5 Molybdenum is in a first bi-layer over the substrate.

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1 28. (New) The optical system of claim 24 wherein the extra thick layer of
2 Silicon is in a third bi-layer over the substrate.

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